

# NPN SILICON RF POWER TRANSISTOR

## DESCRIPTION:

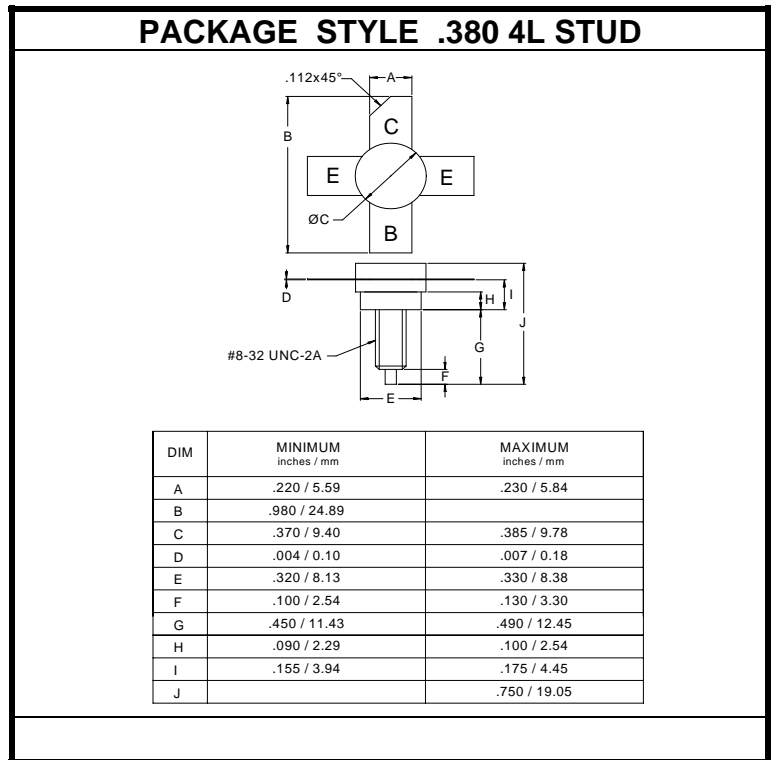
The **ASI BLW31** is an NPN silicon power transistor, designed 175 MHz applications, especially suited for design of wide-band and semi-wide-band VHF amplifiers.

## FEATURES:

- Common Emitter-Class-A, B or C
- $P_G = 9$  dB at 28 W/175 MHz
- **Omnigold™** Metalization System

## MAXIMUM RATINGS

$I_C$	6.0 A
$V_{CESM}$	36 V
$V_{CEO}$	18 V
$V_{EBO}$	4.0 V
$P_{DISS}$	96 W @ $T_{MB} = 25$ °C
$T_J$	-65 °C to +200 °C
$T_{STG}$	-65 °C to +150 °C
$\theta_{JC}$	1.85 °C/W



## CHARACTERISTICS $T_C = 25$ °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
$BV_{CEO}$	$I_C = 100$ mA	18			V
$BV_{CES}$	$I_C = 25$ mA	36			V
$BV_{EBO}$	$I_E = 10$ mA	4.0			V
$I_{CES}$	$V_{CE} = 18$ V			10	mA
$h_{FE}$	$V_{CE} = 5.0$ V $I_C = 3.5$ A	10		80	---
$C_{CC}$ $C_{RE}$ $C_{CS}$	$V_{CB} = 13.5$ V $f = 1.0$ MHz		92 58 2		pF
$P_G$ $\eta_C$	$V_{CC} = 13.5$ V $P_{OUT} = 28$ W $f = 175$ MHz	9.0 60	9.5 70		dB %